Application No.:10/655,806 Docket No.: JCLA11376

AMENDMENT

In The Claims:

Claims 1-3. (canceled)

Claim 4. (previously amended) A method of polishing a wafer, comprising the steps of:

providing a first polishing pad, wherein the first polishing pad comprises a plurality of first abrasive units each fabricated using an adhesive compound with evenly distributed abrasive particles therein;

performing a first polishing operation on the first polishing pad to planarize a wafer;

providing a second polishing pad, wherein the second polishing pad comprises a plurality of second abrasive units each fabricated using an adhesive compound with evenly distributed abrasive particles therein, and the surface of the second abrasive units in contact with the wafer is roughened and the abrasive units are shaped into a triangular cone, hexagonal cone or circular cylinder and set up as an array; and

performing a second polishing operation on the second polishing pad, wherein the second polishing operation is conducted at a rate faster than that of the first polishing operation.

Claim 5. (original) The wafer polishing method of claim 4, wherein material constituting the abrasive particles comprises cerium oxide (CeO_2).

Claim 6. (original) The wafer polishing method of claim 4, wherein material constituting the adhesive compound comprises a resin.

Claims 7-11. (cancelled)

Claim 12 (previously presented) The wafer polishing method of claim 4, wherein the second polishing operation is conducted at least at a same rate as the first polishing operation.

Claim 13. (new) A method of polishing a wafer, comprising the steps of:

providing a first polishing pad with an flat top surface, wherein the first polishing pad comprises a plurality of first abrasive units each fabricated using an adhesive compound with evenly distributed abrasive particles therein;

performing a first polishing operation on the first polishing pad to planarize a wafer until a top surface of the wafer is even, wherein, while the top surface of the wafer is even, the first polishing operation is conducted at a first removal rate;

providing a second polishing pad, wherein the second polishing pad comprises a plurality of second abrasive units each fabricated using an adhesive compound with evenly distributed abrasive particles therein, and the surface of the second abrasive units in contact with the wafer is roughened and the abrasive units are shaped into a triangular cone, hexagonal cone or circular cylinder and set up as an array; and

performing a second polishing operation on the second polishing pad, wherein the second polishing operation is conducted at a second removal rate faster than first removal rate.

Claim 14. (new) The wafer polishing method of claim 13, wherein material constituting the abrasive particles comprises cerium oxide (CeO_2).

Claim 15. (new) The wafer polishing method of claim 13, wherein material constituting the adhesive compound comprises a resin.

Claim 16 (new) The wafer polishing method of claim 13, wherein the second polishing operation is conducted at least at a same removal rate as the first polishing operation.